



DMP4011SPS

PowerDI5060-8

Product Summary

BV _{DSS}	Rds(on) max	I _{D MAX} T _C = +25°C
-40V	10mΩ @ V _{GS} = -10V	-76A
	14mΩ @ V_{GS} = -4.5V	-58A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- **DC-DC Converters**
- **Power Management Functions**
- Analog Switch

Features and Benefits

100% Unclamped Inductive Switch (UIS) Test in Production

P-CHANNEL ENHANCEMENT MODE MOSFET

- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Complaint Part is Available Under Separate Datasheet (DMP4011SPSQ)

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish-100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3

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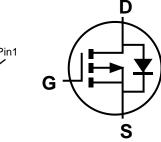
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Weight: 0.097 grams (Approximate)



PowerDI5060-8

Bottom View



Internal Schematic

Top View Pin Configuration ΠD

ПD Πо

ΠD

Ordering Information (Note 4)

Case	Packaging
PowerDI5060-8	2500 / Tape & Reel

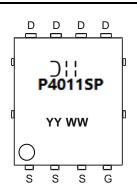
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

Notes:

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



) | | = Manufacturer's Marking P4011SP = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit				
Drain-Source Voltage	V _{DSS}	-40	V				
Gate-Source Voltage			V _{GSS}	±20	V		
Continuous Durin Current (Nate 7) // 10//	Steady	T _C = +25°C	- I _D	-76	A		
Continuous Drain Current (Note 7) $V_{GS} = -10V$	State	T _C = +70°C		-61			
Continuous Drain Current (Note 6) V_{GS} = -10V	Steady State	T _A = +25°C	- I _D	-11.7	А		
		T _A = +70°C		-9.4			
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%		I _{DM}	-300	А			
Maximum Body Diode Continuous Current (Note 6)			Is	-8.9	А		
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			ulsed Source Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	-300	А
Avalanche Current (Note 8) L = 1mH			I _{AS}	-22	А		
Avalanche Energy (Note 8) L = 1mH			E _{AS}	250	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	96.4	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	55	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	1.3	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						·
Drain-Source Breakdown Voltage	BV _{DSS}	-40	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	—	-1	μA	$V_{DS} = -32V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-2.0	-2.5	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance		_	6	10	mΩ	$V_{GS} = -10V, I_D = -9.8A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	10	14	11152	V _{GS} = -4.5V, I _D = -9.8A
Diode Forward Voltage	V _{SD}	_	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	Ciss	_	2747	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz
Output Capacitance	C _{oss}	—	508	—		
Reverse Transfer Capacitance	C _{rss}	—	222	—		
Gate Resistance	Rg	—	21.4	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	25	—		
Total Gate Charge (V _{GS} = -10V)	Qg	—	52	—	nC	V _{DS} = -20V I _D = -9.8A
Gate-Source Charge	Q _{gs}	_	8.5	_	nc	
Gate-Drain Charge	Q _{gd}	—	11.8	—		
Turn-On Delay Time	t _{D(ON)}	_	6.6	—		$\label{eq:VGS} \begin{split} V_{GS} &= \text{-10V}, V_{DD} = \text{-20V}, \\ R_g &= 6\Omega, I_D = \text{-1A} \end{split}$
Turn-On Rise Time	t _R	—	6.5	—		
Turn-Off Delay Time	t _{D(OFF)}	_	222		ns	
Turn-Off Fall Time	t _F	—	138			
Reverse Recovery Time	t _{RR}	_	25		ns	I _F = -9.8A, di/dt = -100A/μs
Reverse Recovery Charge	Q _{RR}	_	17	_	nC	I _F = -9.8A, di/dt = -100A/µs

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).

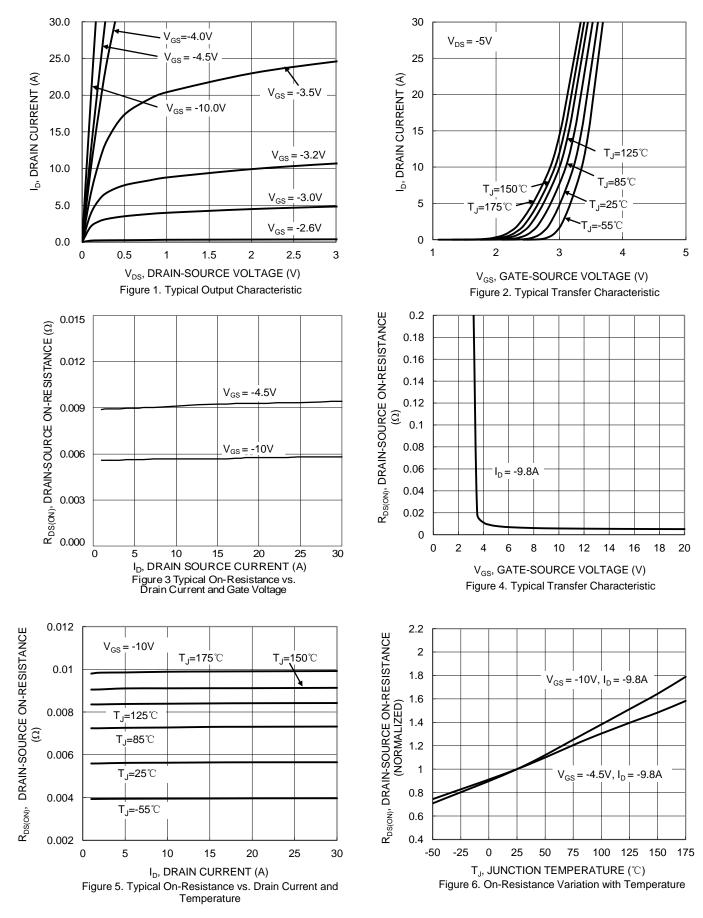
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

9. Short duration pulse test used to minimize self-heating effect.

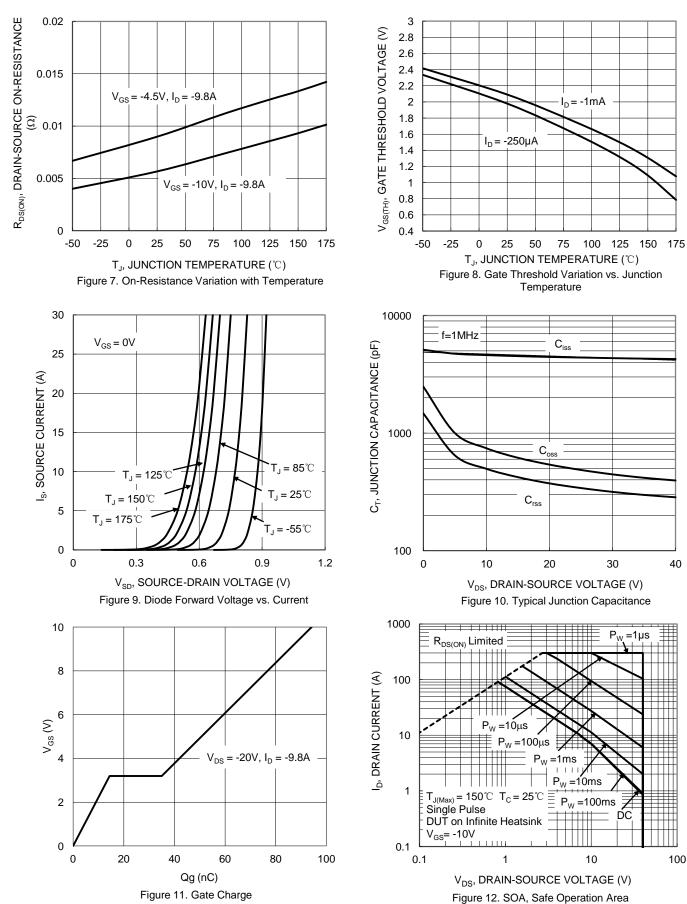
10. Guaranteed by design. Not subject to product testing.



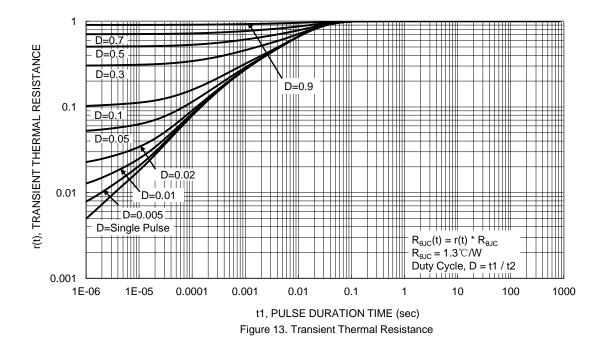
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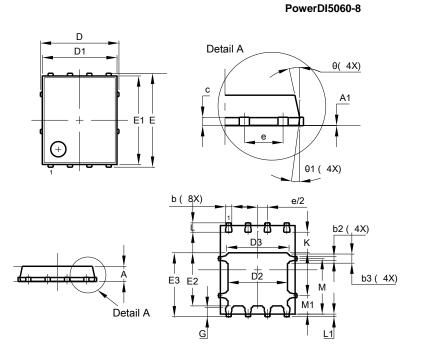






Package Outline Dimensions

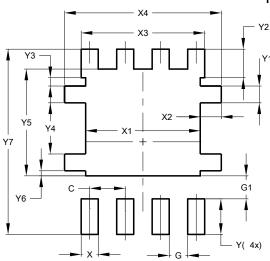
Please see http://www.diodes.com/package-outlines.html for the latest version.



	PowerDI5060-8					
Dim	Min Max Typ					
Α	0.90	1.10	1.00			
A1	0.00	0.05				
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D		5.15 BSC				
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90 4.30 4.1					
E	6.15 BSC					
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е	1.27 BSC					
G	0.51	0.71	0.61			
K	0.51		—			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
Θ	10°	12°	11°			
Θ1	6°	8°	7°			
Al	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI5060-8

Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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